						#3/56/502 Sheet 1 of 1			
Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 728-208 (YOR9-2001-0270 US1)		SERIAL NO. Unassigned		PT0	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				APPLICANTS  LOUIS L. HSU; RAJIV V. JOSHI; and FARIBORZ ASSADERAGHI  100					
			FILING DATE June 13, 2001	GROUP ART UNIT Unassigned					
			U.S. P	ATENT DOCUMENTS					
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		OTHER PRIOR A	RT (Including Auth	or, Title, Date, Pertiner	nt Pages, E	Etc.)			
9		A Novel-Thyrist	A Novel-Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories						
		by Farid Nemati and James D. Plummer, Center for Integrated Systems, Stanford, University, 1999							
(M)		<del></del>	A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device, by Farid Nemati and						
		James D. Plummer, Center for Integrated Systems, Stanford University, 1998							
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* EXAMINER citation	: Initi i if not i	al if reference consider n conformance and not	dered, whether or a considered. Incl	not citation is in confor ude copy of this form wit	mance with h next com	MPEP 609. Dra	w line th pplicant.	rough	